



Clean Versions of Replacement Claims

Please amend claims 1, 4, 11, 13, and 15 to conform to the following clean versions.

A1
1. A magnetic memory cell, comprising:
sense layer for storing a magnetization state that indicates a logic state of the magnetic memory cell;
structure that prevents disruptions to the magnetization state in the sense layer, the structure applying a magnetic field to a set of edge regions of the sense layer in a direction substantially perpendicular to an easy axis of the sense layer.

A2
4. The magnetic memory cell of claim 1, wherein the structure is formed from a permeable ferromagnetic material having an easy axis that is substantially perpendicular to the easy axis of the sense layer.

A3
11. The magnetic memory cell of claim 10, wherein the hard ferromagnetic material is magnetized perpendicular to the easy axis of the sense layer.

A4
13. A magnetic memory cell, comprising:
sense layer for storing a magnetization that indicates a logic state of the magnetic memory cell;
means for providing flux closure for one or more demagnetization fields in the magnetic memory cell and for applying a magnetic field to a set of edge regions of the sense layer in a direction substantially perpendicular to an easy axis of the sense layer.

A6
15. The magnetic memory cell of claim 14, wherein the permeable ferromagnetic material has an easy axis that is

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perpendicular to the easy axis of the sense layer.

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